

HF/VHF POWER MOSFET

N-Channel Enhancement Mode

DESCRIPTION:

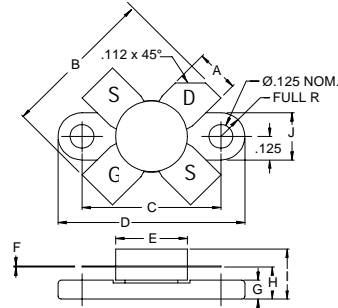
The **ASI SD1905** is Designed for General Purpose Class-A,B Power Amplifier Applications up to 200 MHz.

FEATURES:

- $P_G = 13$ dB Typical at 200 MHz
- Common Source Configuration
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_D	8.4 A
$V_{(BR)DSS}$	65 V
V_{DGR}	65 V
V_{GS}	± 20 V
P_{DISS}	117 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .380 4L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	$I_D = 10$ mA			65			V
I_{DSS}	$V_{DS} = 28$ V	$V_{GS} = 0$ V				5.0	mA
I_{GSS}	$V_{DS} = 0$ V	$V_{GS} = 20$ V				1.0	μA
g_{fs}	$I_D = 10$ A	$V_{DS} = 10$ V		.7			mohs
C_{iss} C_{oss} C_{rss}	$V_{DS} = 28$ V	$V_{GS} = 0$ V	$f = 1.0$ MHz			80 70 20	pF
P_G η_D	$V_{DD} = 28$ V	$I_{DQ} = 25$ mA	$P_{out} = 45$ W $f = 150$ MHz	12 50			dB %